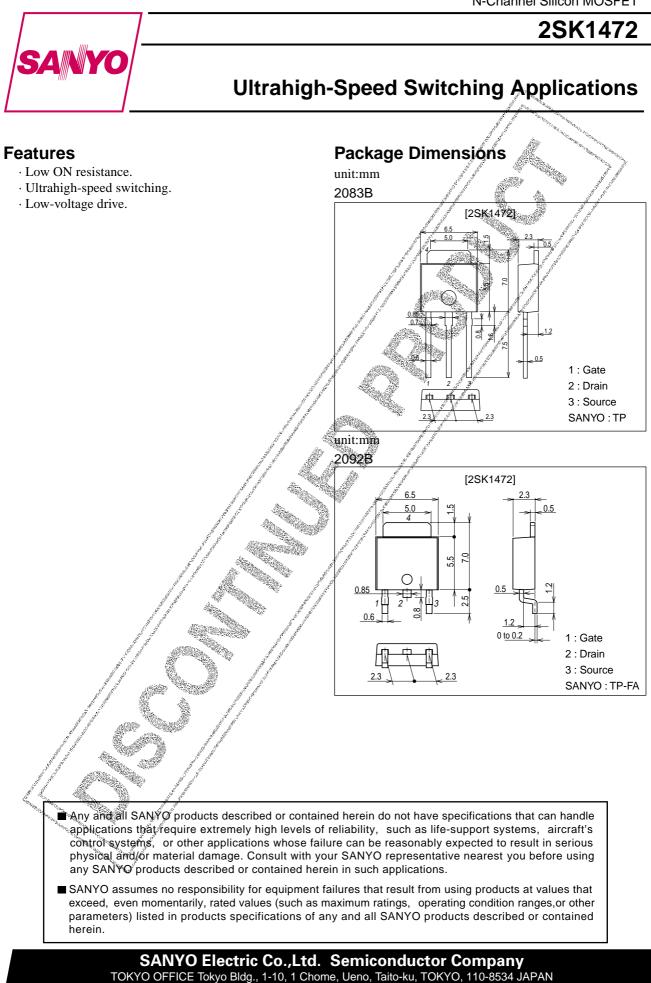
N-Channel Silicon MOSFET



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		60	V
Gate-to-Source Voltage	V _{GSS}		±15	V
Drain Current (DC)	۱ _D		8	A
Drain Current (pulse)	I _{DP}	PW≤10µs, duty cycle≤1%	32	A
Allowable Power Dissipation	PD		/ 🔗 🔨 1.0	W
		Tc=25°C	30	W
Channel Temperature	Tch		150	∫°C
Storage Temperature	Tstg		-55 to +150	°C
Electrical Characteristics a	t Ta = 25°C	·	Sage //	•

Electrical Characteristics at Ta = 25°C

			See.	, ,	1	
Parameter	Symbol	Conditions	. min	Ratings	max	Unit
Drain-to-Source Breakdown Voltage	V _(BR) DSS	I _D =1mA, V _{GS} =0	60	for the second s		V
Gate-to-Source Breakdown Voltage	V(BR)GSS	IG=±100μA, V _{DS} =0	±15	AL OF REAL		V
Zero-Gate Votlage Drain Current	IDSS	V _{DS} =60V, V _{GS} =0	See Sta	έ.	100	μA
Gate-to-Source Leakage Current	IGSS	V _{GS} =±12V, V _{DS} =0	and the second		±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.0		2.0	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =4A	5	8		S
Static Drain-to-Source On-State Resistance	R _{DS(on)} 1	I _D =4A, V _{GS} =10V		60	80	mΩ
Static Drain-to-Source On-State Resistance	R _{DS(on)} 2	ID=4A, VGS=4V		80	110	mΩ
Input Capacitance	Ciss	V _{DS} =20V, f≠1MHz		950		pF
Output Capacitance	Coss	V _{DS} =20V/f=1MHz		250		pF
Reverse Transfer Capacitance	Crss	V _{DS} ⊭20V, f=1MHz		50		pF
Turn-ON Delay Time	^t d(on)	See specified Test Circuit		13		ns
Rise Time	t _r	See specified Test Circuit		30		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit		110		ns
Fall Time	t _f shi shi	See specified Test Circuit		80		ns
Diode Forward Voltage	VSD	IS=8A VGS=0		1.0	1.5	V

Switching Time Test Circuit

